

The documentation and process conversion measures necessary to comply with this revision shall be completed by 22 September 2001.

METRIC

MIL-PRF-19500/620D
 22 June 2001
 SUPERSEDING
 MIL-PRF-19500/620C
 21 June 1998

PERFORMANCE SPECIFICATION

SEMICONDUCTOR DEVICE, HERMETIC, DIODE, SILICON, RECTIFIER,
 SCHOTTKY BARRIER, TYPES 1N5822 AND 1N5822US
 JAN, JANTX, JANTXV, JANJ, JANS, JANHC, AND JANKC

This specification is approved for use by all Departments and Agencies of the Department of Defense.

1. SCOPE

1.1 Scope. This specification covers the performance requirements for silicon, Schottky barrier rectifier diodes. Five levels of product assurance are provided for each device type as specified in MIL-PRF-19500, and two levels of product assurance for die (element evaluation).

1.2 Physical dimensions. See figures 1, 2, and 3 (JANC die) dimensions.

1.3 Maximum ratings.

Types	V_{RWM} (1)	I_{O1} (2)	I_{FSM}	T_{STG}	T_J
	<u>V(pk)</u>	<u>A dc</u>	<u>A(pk)</u>	<u>°C</u>	<u>°C</u>
1N5822, 1N5822US	40	3.0	80	-65 to +150	-65 to +125

(1) Derate linearly at 1.2 V/°C above T_L or $T_{EC} = +90$ °C where T_L is at L = 9.52 mm (.375 inch).

(2) Derate linearly at 43 mA/°C above T_L or $T_{EC} = +55$ °C where T_L is at L = 9.52 mm (.375 inch).

1.4 Primary electrical characteristics. Unless otherwise specified, $T_A = +25$ °C.

Types	Max V_{FM1}	Max V_{FM2}	Max V_{FM3}	Max I_{RM} $V_{RM} = 40$ V dc pulsed method (see 4.5.1)		Max $R_{\theta JL}$ or $R_{\theta JEC}$ 9.52 mm (3.75 inch) lead length or end cap	Max $Z_{\theta JX}$
	$I_{FM} = 1.0$ A	$I_{FM} = 3.0$ A	$I_{FM} = 9.4$ A	$T_J = +25$ °C I_{RM1}	$T_J = +100$ °C I_{RM2}		
	<u>V (pk)</u>	<u>V (pk)</u>	<u>V (pk)</u>	<u>mA</u>	<u>mA</u>	<u>°C/W</u>	<u>°C/W</u>
1N5822	0.40	0.50	0.70	0.10	12.5	30	3.0
1N5822US	0.40	0.50	0.70	0.10	12.5	10	3.0

Beneficial comments (recommendations, additions, deletions) and any pertinent data which may be of use in improving this document should be addressed to: Defense Supply Center, Columbus, ATTN: DSCC/VAC, Post Office Box 3990, Columbus, OH 43216-5000, by using the Standardization Document Improvement Proposal (DD Form 1426) appearing at the end of this document or by letter.

AMSC N/A

FSC 5961

DISTRIBUTION STATEMENT A. Approved for public release; distribution is unlimited.

2. APPLICABLE DOCUMENTS

2.1 General. The documents listed in this section are specified in sections 3 and 4 of this specification. This section does not include documents cited in other sections of this specification or recommended for additional information or as examples. While every effort has been made to ensure the completeness of this list, document users are cautioned that they must meet all specified requirements documents cited in sections 3 and 4 of this specification, whether or not they are listed.

2.2 Government documents.

2.2.1 Specifications, standards, and handbooks. The following specifications, standards, and handbooks form a part of this document to the extent specified herein. Unless otherwise specified, the issues of these documents are those listed in the issue of the Department of Defense Index of Specifications and Standards (DoDISS) and supplement thereto, cited in the solicitation (see 6.2).

SPECIFICATION

DEPARTMENT OF DEFENSE

MIL-PRF-19500 - Semiconductor Devices, General Specification for.

STANDARD

DEPARTMENT OF DEFENSE

MIL-STD-750 - Test Methods for Semiconductor Devices.

(Unless otherwise indicated, copies of the above specifications, standards, and handbooks are available from the Document Automation and Production Services (DAPS), Building 4D (DPM-DODSSP), 700 Robbins Avenue, Philadelphia, PA 19111-5094.)

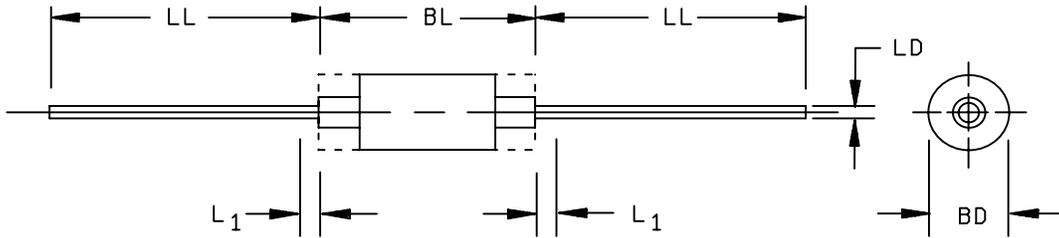
2.3 Order of precedence. In the event of a conflict between the text of this document and the references cited herein, the text of this document takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.

3. REQUIREMENTS

3.1 General. The requirements for acquiring the product described herein shall consist of this document and MIL-PRF-19500.

3.2 Qualification. Devices furnished under this specification shall be products that are manufactured by a manufacturer authorized by the qualifying activity for listing on the applicable qualified manufacturer's list (QML) before contract award (see 4.2 and 6.3).

3.3 Abbreviations, symbols, and definitions. Abbreviations, symbols, and definitions used herein shall be as specified in MIL-PRF-19500.

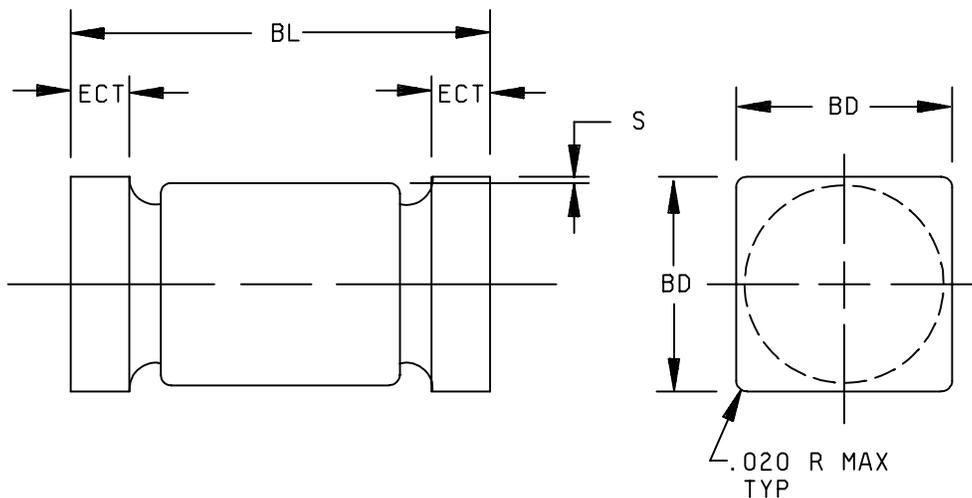


Symbol	Dimensions				Notes
	Millimeters		Inches		
	Min	Max	Min	Max	
LD	0.91	1.07	.036	.042	
BD	2.92	3.68	.115	.145	3
BL	3.30	4.95	.130	.195	
LL	22.86	33.02	.900	1.300	
L ₁		0.76		.030	4

NOTES:

1. Dimensions are in millimeters.
2. Inch-pound equivalents are given for general information only.
3. Symbol BD shall be measured at the largest diameter.
4. Lead diameter is not controlled in this zone to allow for flash, lead finish build-up, and mirror irregularities other than heat slugs.

FIGURE 1. Physical dimensions of 1N5822.

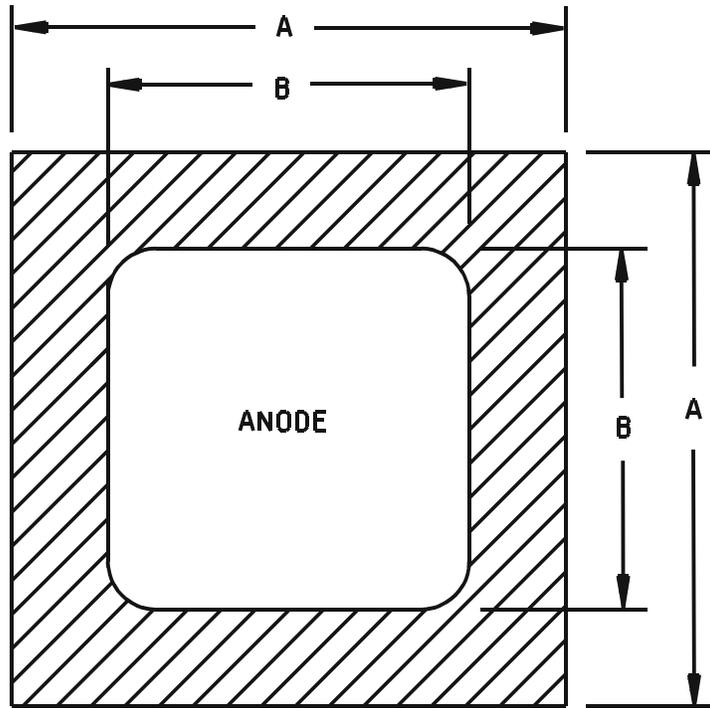


Symbol	Dimensions			
	Millimeters		Inches	
	Min	Max	Min	Max
BL	5.08	5.72	.200	.225
BD	3.48	3.76	.137	.148
ECT	0.48	0.71	.019	.028
S	0.08		.003	

NOTES:

1. Dimensions are in millimeters.
2. Inch-pound equivalents are given for general information only.

FIGURE 2. Physical dimensions of surface mount family, 1N5822US (D-5B).



Symbol	Dimensions			
	Millimeters		Inches	
	Min	Max	Min	Max
A	1.57	1.63	.062	.064
B	1.32	1.37	.052	.054

Design data

Metallization:

Top: (Anode) AL

Back: (Cathode). Au

AL thickness 25,000 Å minimum.

Gold thickness 4,000 Å minimum.

Chip thickness 0.254 mm (10 mils) ± .051 (± 2 mils).

FIGURE 3. JANC (A-version) die dimensions.

3.4 Interface and physical dimensions. Interface and physical dimensions shall be as specified in MIL-PRF-19500, and on figures 1 (axial package), 2 (surface mount), and 3 (die). The US Government's preferred system of measurement is the metric SI system. However, since this item was originally designed using inch-pound units of measurement, in the event of conflict between the metric and inch-pound units, the inch-pound units shall take precedence.

3.4.1 Lead material and finish. Lead material shall be copper clad steel with a minimum of 70 percent copper by weight. Lead finish shall be solderable in accordance with MIL-PRF-19500, MIL-STD-750, and herein. Where a choice of lead finish is desired, it shall be specified in the acquisition document (see 6.2).

3.4.2 Diode construction. These devices shall be constructed in a manner and using materials which enable the diodes to meet the applicable requirements of MIL-PRF-19500 and this document.

3.4.2.1 Surface mount. The surface mount (US) version shall be considered structurally identical to the non surface mount version except for lead attach.

3.5 Marking. Marking shall be in accordance with MIL-PRF-19500. At the option of the manufacturer, marking may be omitted from the body, but shall be retained on the initial container.

3.5.1 Marking for surface mount (US) devices. Surface mount (US) suffix parts are to be marked with the polarity identification. Initial container package marking will be in accordance with MIL-PRF-19500.

3.6 Electrical performance characteristics. Unless otherwise specified herein, the electrical performance characteristics are as specified in 1.3.

3.7 Electrical test requirements. The electrical test requirements shall be group A as specified herein.

3.8 Workmanship. Semiconductor devices shall be processed in such a manner as to be uniform in quality and shall be free from other defects that will affect life, serviceability, or appearance.

4. VERIFICATION

4.1 Classification of inspections. The inspection requirements specified herein are classified as follows:

- a. Qualification inspection (see 4.2).
- b. Screening (see 4.3).
- c. Conformance inspection (see 4.4).

4.2 Qualification inspection. Qualification inspection shall be in accordance with MIL-PRF-19500 and as specified herein..

4.2.1 Group E inspection. Group E inspection shall be conducted in accordance with MIL-PRF-19500 and 4.4.4 herein.

4.2.2 JANHC and JANKC devices. Qualification for JANHC and JANKC devices shall be in accordance with MIL-PRF-19500. This testing may be performed in a TO-5 package in lieu of the axial leaded package.

4.2.3 JANJ devices. For JANJ level, 3.3.1 through 3.3.1.3 of MIL-PRF-19500 shall apply, except as modified herein. Supplier imposed requirements as well as alternate screens, procedures, and/or controls shall be documented in the QM plan and must be submitted to the qualifying activity for approval. When alternate screens, procedures, and/or controls are used, in lieu of the JANJ screens herein, equivalency shall be proven and documented in the QM plan. Radiation characterization may be submitted in the QM plan at the option of the manufacturer, however, 3.3.1.1 of MIL-PRF-19500 is not required. Die lot control and rework shall be in accordance with 3.13 and D 3.13.2.1 for JANS level of MIL-STD-19500. Lot formation and conformance inspection requirements for JANJ shall be those used for JANTXV devices as a minimum.

4.2.4 JANJ qualification. For JANJ qualification, 4.4.2.1 herein shall be performed as required by the qualifying activity.

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4.3 Screening (JAN, JANTX, JANTXV, JANJ, and JANS levels only). Screening shall be in accordance with table IV of MIL-PRF-19500, and as specified herein. The following measurements shall be made in accordance with table I herein. Devices that exceed the limits of table I herein shall not be acceptable.

Screen (see table IV of MIL-PRF-19500)	Measurement	
	JANS level	JANJ level
1a 1b	Required Required	Not required Required
2	Not required	Not required
3a 3b (1) 3c	Required Not applicable Required (see 4.3.3)	Required Not applicable Required (see 4.3.3)
4, 5, 6 and 7a	Not applicable	Not applicable
7b	Required	Required
8	Required	Not required
9	Required I_{R1} and V_{F2}	Required I_{R1} and V_{F2}
(2) 10	Required $T_A = +90^\circ\text{C}$; $V_{RWM} = 40 \text{ V(pk)}$; $I_O = 0$, half sine wave, $f = 60 \text{ Hz}$	Required $T_A = +90^\circ\text{C}$; $V_{RWM} = 40 \text{ V(pk)}$; $I_O = 0$, half sine wave, $f = 60 \text{ Hz}$
11	Required $\Delta I_{R1} \leq 100$ percent of initial reading or 0.05 mA whichever is greater. $\Delta V_{FM2} \leq \pm 50 \text{ mV dc}$.	Required $\Delta I_{R1} \leq 100$ percent of initial reading or 0.05 mA whichever is greater. $\Delta V_{FM2} \leq \pm 50 \text{ mV dc}$.
12	Required See 4.3.2.	Required See 4.3.2.
13	Required Subgroup 2 of table I herein; $\Delta I_{R1} \leq 100$ percent of initial reading or 0.05 mA whichever is greater; $\Delta V_{FM2} \leq \pm 50 \text{ mV dc}$ scope display evaluation (see 4.5.3).	Required Subgroup 2 of table I herein; $\Delta I_{R1} \leq 100$ percent of initial reading or 0.05 mA whichever is greater; $\Delta V_{FM2} \leq \pm 50 \text{ mV dc}$ scope display evaluation (see 4.5.3).
14a 14b	Not applicable Optional (3)	Not applicable Optional (3)
15	Required	Required. Attributes data only. Film or non-film techniques may be utilized
16	Required	Required
17	Not applicable	Required, subgroup 2 of table I herein

See notes at end of table.

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4.3 Screening (JAN, JANTX, JANTXV, JANJ, and JANS levels only) - continued.

Screen (see table IV of MIL-PRF-19500)	Measurement	
	JANTXV and JANTX level	JAN level
1a 1b	Not required Required (JANTXV only)	Not required Not required
2	Not required	Not required
3a 3b (1) 3c	Required Not applicable Required (see 4.3.3)	Required in accordance with MIL-PRF-19500, JANTX level Not applicable Required (see 4.3.3)
4, 5, 6 and 7a	Not applicable	Not applicable
7b	Required	Not required
8	Not required	Not required
9	Not applicable	Not applicable
(2) 10	Required $T_A = +90^\circ\text{C}$; $V_{RWM} = 40 \text{ V(pk)}$; $I_O = 0$, half sine wave, $f = 60 \text{ Hz}$	Not applicable
11	Required I_{R1} and V_{FM2}	Not applicable
12	Required See 4.3.2, $t = 48 \text{ hours}$	Not applicable
13	Required Subgroup 2 of table I herein; $\Delta I_{R1} \leq 100$ percent of initial reading or 0.05 mA whichever is greater; $V_{FM2} \leq \pm 50 \text{ mV dc}$; scope display evaluation (see 4.5.3).	Not applicable
14a 14b	Not applicable Optional (3)	Not applicable Not required
15 and 16	Not required	Not required
17	Not applicable	Not applicable

- (1) Thermal impedance shall be performed any time after sealing provided temperature cycling is performed in accordance with table IV of MIL-PRF-19500, screen 3 prior to this thermal test.
- (2) Junction temperature (T_J) is not to exceed 115°C at V_{RWM} . T_J is affected by the device mounting thermal resistance when parasitic power is generated by the temperature dependent leakage current. Until this leakage becomes significant near thermal runaway, T_J remains approximately equal to T_A or T_J for $I_O = 0$.
- (3) In accordance with MIL-PRF-19500.

4.3.1 Screening (JANHC or JANKC). Screening of die shall be in accordance with MIL-PRF-19500.

4.3.2 Burn-in conditions. Burn-in conditions are as follows: $I_F = 3$ A dc minimum. T_A = room ambient as defined in the general requirements of MIL-STD-750. Mounting and test conditions shall be in accordance with method 1038 of MIL-STD-750, test condition B.

4.3.3 Thermal impedance. Thermal impedance $Z_{\theta JX}$ measurements shall be performed in accordance with method 3101 of MIL-STD-750, to identify and remove atypical devices.

4.4 Conformance inspection. Conformance inspection shall be in accordance with MIL-PRF-19500 and as specified herein.

4.4.1 Group A inspection. Group A inspection shall be conducted in accordance with table V of MIL-PRF-19500, and table I herein. The following test conditions shall be used for $Z_{\theta JX}$, group A inspection:

- a. I_M measurement current..... 1 mA to 10 mA.
- b. I_H forward heating current 10 A to 20 A.
- c. t_H heating time 10 ms.
- d. t_{MD} measurement delay time..... 100 μ s maximum.

4.4.2 Group B inspection. Group B inspection shall be conducted in accordance with the conditions specified for subgroup testing in tables VIa and VIb (JANS, JANJ, JAN, JANTX, and JANTXV) of MIL-PRF-19500 and as follows. Electrical measurements (end-points) shall be in accordance with table I, group A, subgroup 2 herein.

4.4.2.1 Group B inspection, table VIa (JANS) of MIL-PRF-19500.

<u>Subgroup</u>	<u>Method</u>	<u>Condition</u>
3	4066	$I_{FSM} = 80$ A (pk), condition A 2, $I_O = 3$ A dc; T_A = room ambient as defined in 4.5 of MIL-STD-750; 5 surges of 8.3 ms each at 1 minute intervals.
4	1036	$I_F = 3.0$ A dc; T_A = room ambient as defined in the general requirements of MIL-STD-750; $t_{on} = t_{off} = 3$ minutes minimum for 2,000 cycles.
5	1038	$T_A = +90^\circ\text{C}$ minimum, $V_{RWM} = 40$ V(pk); $I_O = 0$, half sine wave, $f = 60\text{Hz}$, T_A adjusted to achieve $T_J = +110^\circ\text{C}$ minimum.
6	3101	$R_{\theta JL} = 30^\circ\text{C/W}$; $L = 9.52$ mm (.375 inch) lead length (non-surface mount). $R_{\theta JEC} = 10^\circ\text{C/W}$ (surface mount).

4.4.2.2 Group B inspection, table VIb (JAN, JANJ, JANTX, and JANTXV) of MIL-PRF-19500.

<u>Subgroup</u>	<u>Method</u>	<u>Condition</u>
2	4066	$I_{FSM} = 80$ A (pk), condition A 2, $I_O = 3$ A dc; T_A = room ambient as defined in 4.5 of MIL-STD-750; 5 surges of 8.3 ms each at 1 minute intervals.
3	1038	$T_A = +90^\circ\text{C}$ minimum, $V_{RWM} = 40$ V(pk); $I_O = 0$, half sine wave, $f = 60\text{Hz}$, T_A adjusted to achieve $T_J = +110^\circ\text{C}$ minimum.
4	2075	

4.4.3 Group C inspection. Group C inspection shall be conducted in accordance with the conditions specified for subgroup testing in table VII of MIL-PRF-19500. Electrical measurements (end-points) shall be in accordance with table I, group A, subgroup 2 herein.

4.4.3.1 Group C inspection, table VII of MIL-PRF-19500.

<u>Subgroup</u>	<u>Method</u>	<u>Condition</u>
2	2036	Tension: Test condition A; weight = 20 pounds; $t = 15$ seconds. Lead fatigue: Test condition E; weight 1 pounds. NOTE: Both tension and lead fatigue are not applicable for US devices.
6	1038	$T_A = +90^\circ\text{C}$ minimum, $V_{RWM} = 40$ V(pk); $I_O = 0$, half sine wave, $f = 60\text{Hz}$, T_A adjusted to achieve $T_J = +110^\circ\text{C}$ minimum.

4.4.4 Group E inspection. Group E inspection shall be conducted in accordance with MIL-PRF-19500 and the conditions for subgroup testing in table II herein. Electrical measurements (end-points) shall be in accordance with table I, group A, subgroup 2 herein.

4.5 Methods of inspection. Methods of inspection shall be as specified in the appropriate tables and as follows.

4.5.1 Pulse measurements. Conditions for pulse measurement shall be as specified in section 4 of MIL-STD-750.

4.5.2 Steady-state operation life. This test shall be conducted with a half-sine wave of the specified peak voltage impressed across the diode in the reverse direction followed by a half-sine waveform of the specified average rectified current. The forward conduction angle of the rectified current shall not be greater than 180° nor less than 150°.

4.5.3 Scope display evaluation. Scope display evaluation shall be sharp and stable in accordance with method 4023 of MIL-STD-750. Scope display may be performed on ATE (automatic test equipment) for screening only with the approval of the qualifying activity. Scope display in group A shall be performed on an oscilloscope. 100 percent scope test is required in the event of a group A failure, however group A resubmission criteria applies.

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TABLE I. Group A inspection.

Inspection ^{1/}	MIL-STD-750		Symbol	Limits		Unit
	Method	Conditions		Min	Max	
<u>Subgroup 1</u>						
Visual and mechanical examination	2071					
<u>Subgroup 2</u>						
Thermal impedance	3101	See 4.3.3	Z _{θJX}		3.0	°C/W
Forward voltage	4011	I _{FM} = 1.0 A (pk) pulse method (see 4.5.1)	V _{FM1}		0.40	V
	4011	I _{FM} = 3.0 A (pk) pulse method (see 4.5.1)	V _{FM2}		0.50	V
	4011	I _{FM} = 9.4 A (pk) pulse method (see 4.5.1)	V _{FM3}		0.70	V
Reverse current leakage	4016	V _{RM} = 40 V (pk) pulse method (see 4.5.1)	I _{RM1}		0.10	mA
<u>Subgroup 3</u>						
High temperature operation:		T _A = +100°C				
Reverse current leakage	4016	V _{RM} = 40 V (pk) pulse method (see 4.5.1)	I _{RM2}		12.5	mA
Forward voltage	4011	I _F = 3.0 A (pk) pulse method (see 4.5.1)	V _{FM4}		0.47	V
Low temperature operation:		T _A = -55°C				
Reverse current leakage	4016	V _{RM} = 40 V (pk) pulse method (see 4.5.1)	I _{RM3}		0.40	mA
Forward voltage	4011	I _F = 3.0 A (pk) pulse method (see 4.5.1)	V _{FM5}		0.62	V
<u>Subgroup 4</u>						
Scope display	4023	Sharp and stable (see 4.5.3); sample plan: n = 116, c = 0				
<u>Subgroups 5, 6, and 7</u>						
Not applicable						

^{1/} For sampling plan, see MIL-PRF-19500.

TABLE II. Group E inspection (all quality levels) for qualification only. ^{1/}

Inspection	MIL-STD-750		Sampling plan
	Method	Conditions	
<u>Subgroup 1</u>			
Thermal shock (temperature cycling)	1051	500 cycles	22 devices c = 0
Hermetic seal	1071	Test condition E	
Electrical measurement		See table I, group A, subgroup 2.	
<u>Subgroup 2</u>			
Steady-state reverse bias	1038	Test condition A, 1,000 hours, see 4.4.3.1, group C, subgroup 6.	22 devices c = 0
Electrical measurement		See table I, group A, subgroup 2	
<u>Subgroup 3</u>			
Not applicable			
<u>Subgroup 4</u>			
Thermal resistance, (forward voltage drop diode method)	4081 or 3101	$R_{\theta JL} = 30^{\circ}\text{C/W}$ maximum at 9.52 mm (.375 inch) lead length; $R_{\theta JEC} = 10^{\circ}\text{C/W}$ maximum; method 3101 in accordance with 4.3.3 except $I_H = 3\text{ A}$ and $T_H = 20\text{ s}$ (minimum)	22 devices c = 0
<u>Subgroup 5</u>			
Not applicable			
<u>Subgroup 6</u>			
Not applicable			

^{1/} For initial design and process change verification only (one time testing).

5. PACKAGING

5.1 Packaging. For acquisition purposes, the packaging requirements shall be as specified in the contract or order (see 6.2). When actual packaging of materiel is to be performed by DoD personnel, these personnel need to contact the responsible packaging activity to ascertain requisite packaging requirements. Packaging requirements are maintained by the Inventory Control Point's packaging activity within the Military Department or Defense Agency, or within the Military Department's System Command. Packaging data retrieval is available from the managing Military Department's or Defense Agency's automated packaging files, CD-ROM products, or by contacting the responsible packaging activity.

6. NOTES

(This section contains information of a general or explanatory nature that may be helpful, but is not mandatory.)

6.1 Intended use. The notes specified in MIL-PRF-19500 are applicable to this specification.

6.2 Acquisition requirements. The acquisition requirements are as specified in MIL-PRF-19500.

6.3 Qualification. With respect to products requiring qualification, awards will be made only for products which are, at the time of award of contract, qualified for inclusion in Qualified Manufacturers' List (QML) whether or not such products have actually been so listed by that date. The attention of the contractors is called to these requirements, and manufacturers are urged to arrange to have the products that they propose to offer to the Federal Government tested for qualification in order that they may be eligible to be awarded contracts or orders for the products covered by this specification. Information pertaining to qualification of products may be obtained from Defense Supply Center, Columbus, ATTN: DSCC/VQE, P.O. Box 3990, Columbus, OH 43216-5000.

6.4 Suppliers of die. The qualified die suppliers with the applicable letter version (e.g., JANHCA1N5822) will be identified on the QML.

JANC ordering information		
PIN	Manufacturer	
	55801	
1N5822	JANHCA1N5822 JANKCA1N5822	

6.5 Changes from previous issue. Marginal notations are not used in this revision to identify changes with respect to the previous issue due to the extent of the changes.

Custodians:
 Army - CR
 Navy - NW
 Air Force - 11
 NASA - NA
 DLA - CC

Preparing activity:
 DLA - CC
 (Project 5961-2416)

Review activities:
 Army - AR, MI, SM
 Navy - AS, MC
 Air Force - 19

STANDARDIZATION DOCUMENT IMPROVEMENT PROPOSAL

INSTRUCTIONS

1. The preparing activity must complete blocks 1, 2, 3, and 8. In block 1, both the document number and revision letter should be given.
2. The submitter of this form must complete blocks 4, 5, 6, and 7.
3. The preparing activity must provide a reply within 30 days from receipt of the form.

NOTE: This form may not be used to request copies of documents, nor to request waivers, or clarification of requirements on current contracts. Comments submitted on this form do not constitute or imply authorization to waive any portion of the referenced document(s) or to amend contractual requirements.

I RECOMMEND A CHANGE:	1. DOCUMENT NUMBER MIL-PRF-19500/620D	2. DOCUMENT DATE 22 June 2001
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3. DOCUMENT TITLE
SEMICONDUCTOR DEVICE, HERMETIC, DIODE, SILICON, RECTIFIER, SCHOTTKY BARRIER, TYPES 1N5822 AND 1N5822US JAN, JANTX, JANTXV, JANJ, JANS, JANHC, AND JANKC

4. NATURE OF CHANGE (Identify paragraph number and include proposed rewrite, if possible. Attach extra sheets as needed.)

5. REASON FOR RECOMMENDATION

6. SUBMITTER

a. NAME (Last, First, Middle initial)	b. ORGANIZATION	
c. ADDRESS (Include Zip Code)	d. TELEPHONE (Include Area Code) COMMERCIAL DSN FAX EMAIL	7. DATE SUBMITTED

8. PREPARING ACTIVITY

a. Point of Contact Alan Barone	b. TELEPHONE Commercial DSN FAX EMAIL 614-692-0510 850-0510 614-692-6939 alan.barone@dscd.dla.mil		
c. ADDRESS Defense Supply Center Columbus, ATTN: DSCC-VAC, P.O. Box 3990, Columbus, OH 43216-5000	IF YOU DO NOT RECEIVE A REPLY WITHIN 45 DAYS, CONTACT: Defense Standardization Program Office (DLSC-LM) 8725 John J. Kingman, Suite 2533, Fort Belvoir, VA 22060-6221 Telephone (703) 767-6888 DSN 427-6888		